

PNP General Purpose Transistor

NST857BF3T5G

The NST857BF3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE} , 220–475
- Low $V_{CE(sat)}$, ≤ -0.3 V
- Reduces Board Space
- This is a Pb-Free Device

MAXIMUM RATINGS

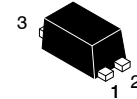
Symbol	Rating	Value	Unit
V_{CEO}	Collector – Emitter Voltage	–45	Vdc
V_{CBO}	Collector – Base Voltage	–50	Vdc
V_{EBO}	Emitter – Base Voltage	–5.0	Vdc
I_C	Collector Current – Continuous	–100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

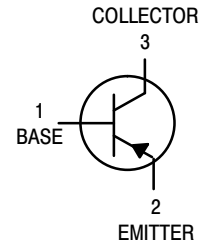
THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
P_D (Note 1)	Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C	290 2.3	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$ (Note 1)	Thermal Resistance, Junction-to-Ambient	432	$^\circ\text{C}/\text{W}$
P_D (Note 2)	Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C	347 2.8	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$ (Note 2)	Thermal Resistance, Junction-to-Ambient	360	$^\circ\text{C}/\text{W}$
$R_{\psi JL}$ (Note 2)	Thermal Resistance, Junction-to-Lead 3	143	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Junction and Storage Temperature Range	–55 to +150	$^\circ\text{C}$

1. 100 mm² 1 oz, copper traces.
2. 500 mm² 1 oz, copper traces.

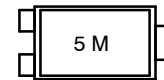


SOT-1123
CASE 524AA
STYLE 1



NST857BF3T5G

MARKING DIAGRAM



5 = Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NST857BF3T5G	SOT-1123 (Pb-Free)	8,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

NST857BF3T5G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector–Emitter Breakdown Voltage ($I_C = -10\text{ mA}$)	-45	-	-	V
$V_{(BR)CES}$	Collector–Emitter Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$, $V_{EB} = 0$)	-50	-	-	V
$V_{(BR)CBO}$	Collector–Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$)	-50	-	-	V
$V_{(BR)EBO}$	Emitter–Base Breakdown Voltage ($I_E = -1.0\text{ }\mu\text{A}$)	-5.0	-	-	V
I_{CBO}	Collector Cutoff Current ($V_{CB} = -30\text{ V}$) ($V_{CB} = -30\text{ V}$, $T_A = 150^\circ\text{C}$)	-	-	-15 -4.0	nA μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain ($I_C = -10\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ V}$) ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$)	- 220	150 290	- 475	-
$V_{CE(sat)}$	Collector–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$)	- -	- -	-0.3 -0.7	V
$V_{BE(sat)}$	Base–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$)	- -	-0.7 -0.9	- -	V
$V_{BE(on)}$	Base–Emitter On Voltage ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ V}$)	-0.6 -	- -	-0.75 -0.82	V

SMALL–SIGNAL CHARACTERISTICS

f_T	Current–Gain – Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	100	-	-	MHz
C_{obo}	Output Capacitance ($V_{CB} = -10\text{ V}$, $f = 1.0\text{ MHz}$)	-	-	4.5	pF
C_{ibo}	Input Capacitance ($V_{EB} = -0.5\text{ V}$, $I_C = 0\text{ mA}$, $f = 1.0\text{ MHz}$)	-	-	10	pF
NF	Noise Figure ($I_C = -0.2\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	-	-	10	dB

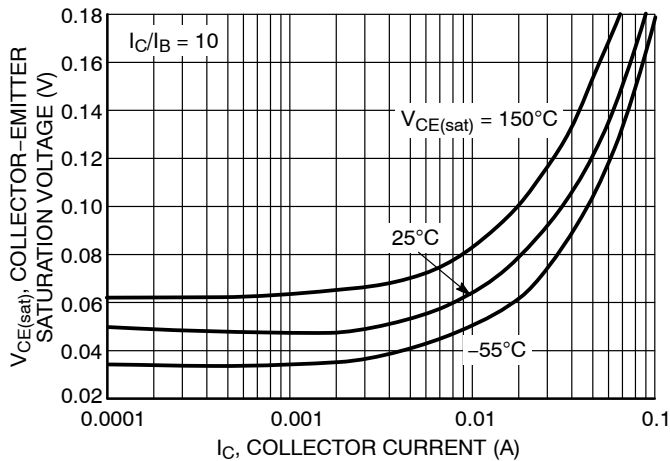


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

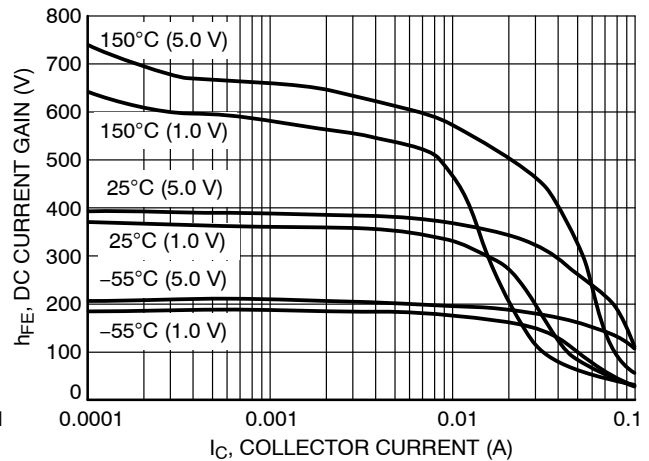


Figure 2. DC Current Gain vs. Collector Current

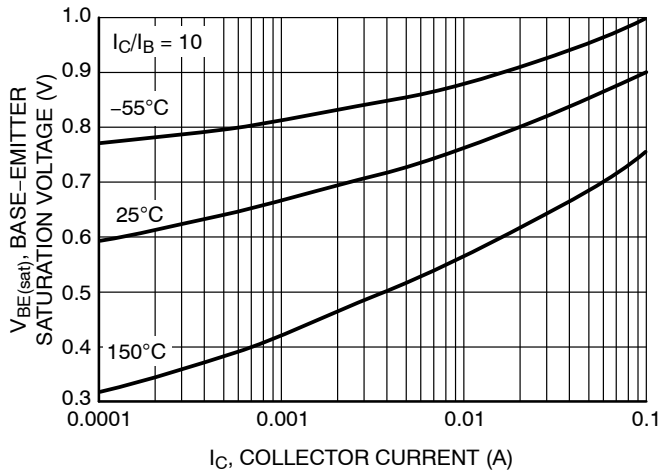


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

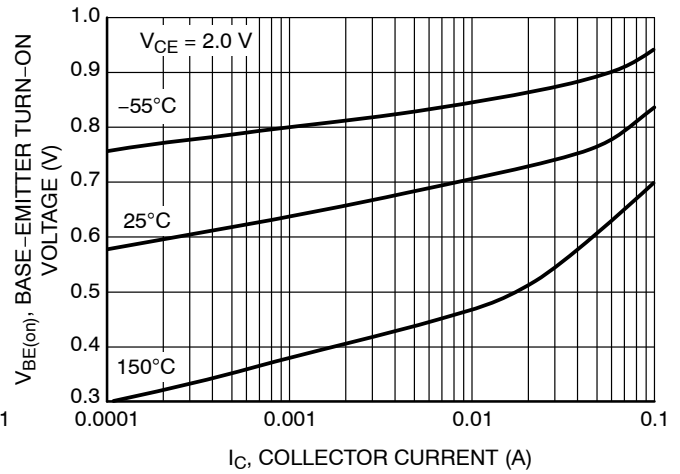


Figure 4. Base Emitter Turn-On Voltage vs. Collector Current

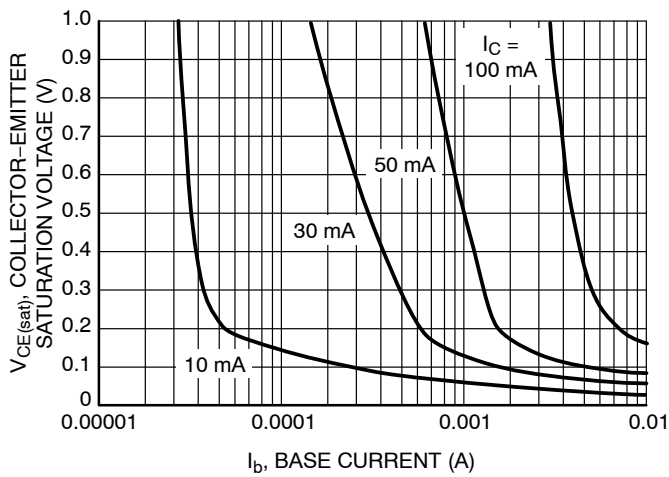


Figure 5. Saturation Region

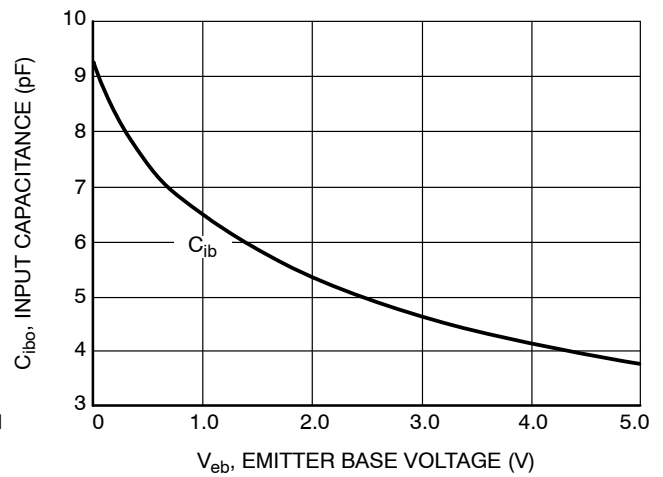


Figure 6. Input Capacitance

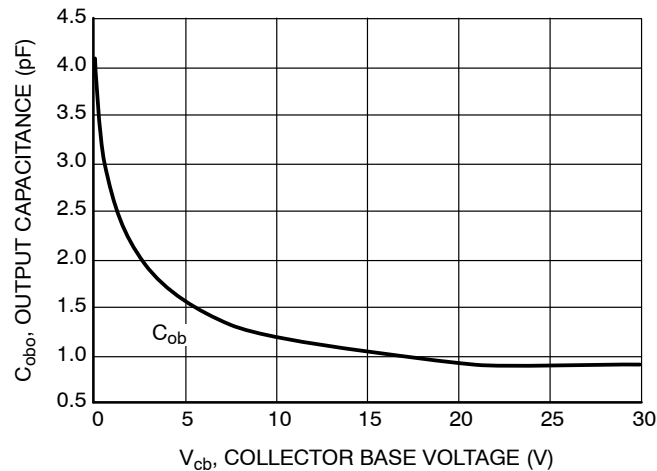
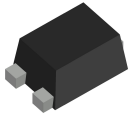
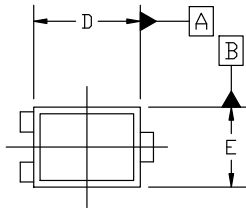


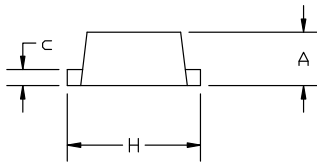
Figure 7. Output Capacitance


SOT-1123 0.80x0.60x0.37, 0.35P
CASE 524AA
ISSUE D

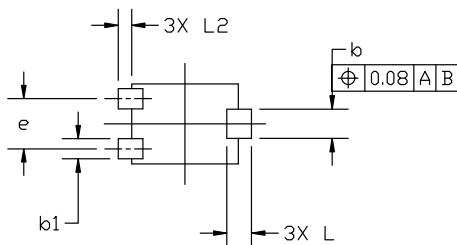
DATE 18 JAN 2024



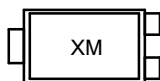
TOP VIEW



SIDE VIEW



BOTTOM VIEW

GENERIC
MARKING DIAGRAM*

X = Specific Device Code
M = Date Code

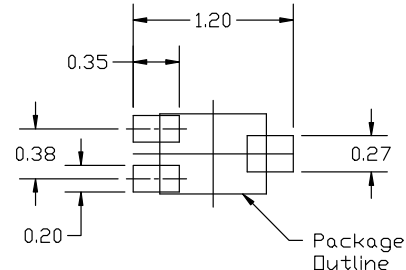
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS

DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.15	0.22	0.28
b1	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.75	0.80	0.85
E	0.55	0.60	0.65
e	0.35	0.38	0.40
H	0.950	1.000	1.050
L	0.185 REF		
L2	0.05	0.10	0.15


RECOMMENDED
MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERM/D.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

DOCUMENT NUMBER: 98AON23134D

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DESCRIPTION: SOT-1123 0.80x0.60x0.37, 0.35P

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